

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
85V	2.2m Ω @10V	260A

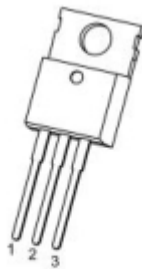
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Applications

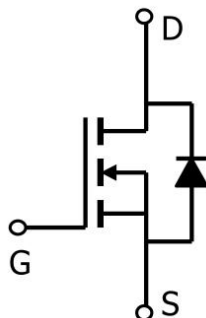
- Power switching application
- DC-DC Converter
- Uninterruptible power supply

Package

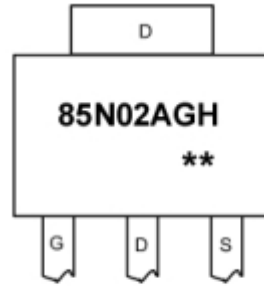


TO-220-3L-C(1:G 2:D 3:S)

Circuit diagram



Marking



85N02AGH : Product code
****** : Week code

Absolute maximum ratings

(T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain source voltage	V _{DS}	85	V
Gate source voltage	V _{GS}	±20	V
Continuous drain current(T _c =25°C)	I _D	260	A
Pulsed drain current	I _{DM}	1040	A
Power dissipation(T _c =25°C)	P _D	300	W
Single pulsed avalanche energy ¹⁾	E _{AS}	375	mJ
Thermal resistance, junction-case	R _{θJC}	0.42	°C/W
Operation and storage temperature	T _J , T _{STG}	-55 to 150	°C

Electrical characteristics

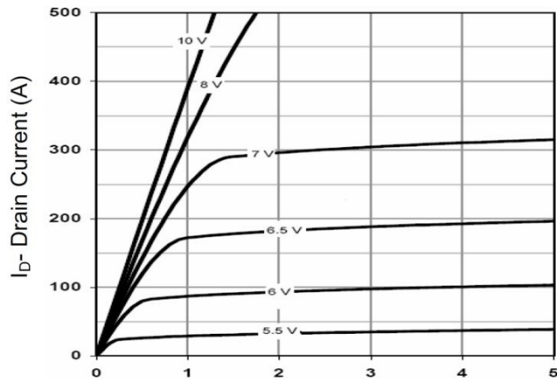
(T_A=25°C, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV (BR)DSS	V _{GS} = 0V, I _D =250μA	85			V
Drain Cut-Off Current	I _{DSS}	V _{DS} =68V, V _{GS} = 0V			1	uA
Gate-Body Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±0.1	uA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	2.5	3.0	3.5	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A		2.2	2.8	mΩ
Dynamic Characteristics						
Input capacitance	C _{iss}	V _{DS} =40V, V _{GS} =0V, f=1MHz		9860		pF
Output capacitance	C _{Oss}			1670		
Reverse transfer capacitance	C _{rss}			76		
Switching Characteristics						
Total Gate Charge	Q _g	V _{DS} =40V, V _{GS} =10V, I _D =165A		143		pF
Gate-Source Charge	Q _{gs}			51		
Gate-Drain Charge	Q _{gd}			25		
Turn-on Delay Time	T _{d(on)}	V _{GS} =10V, V _{DS} =40V, I _D =165A, R _G =1.6Ω		27		nS
Turn-on Rise Time	T _r			75		
Turn-Off Delay Time	T _{d(off)}			86		
Turn-Off Fall Time	t _f			35		
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 1A, V _{GS} = 0V			1.2	V

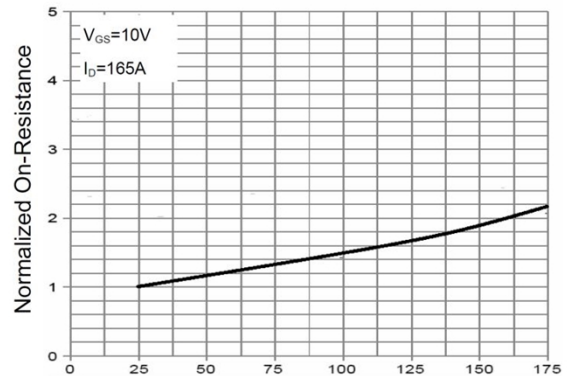
Note:

1. E AS is tested at starting T_j = 25°C, V_{DD} = 45V, V_{GS} = 10V, L = 0.1mH, R_G = 25Ω;

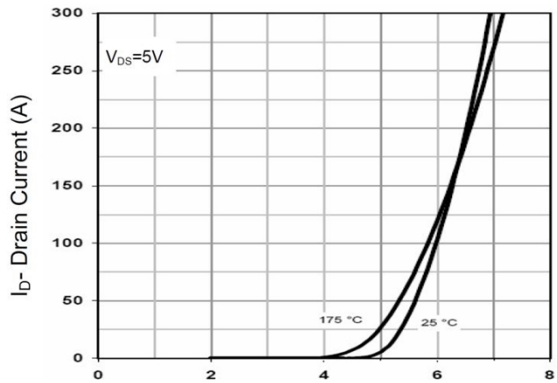
Typical Characteristics



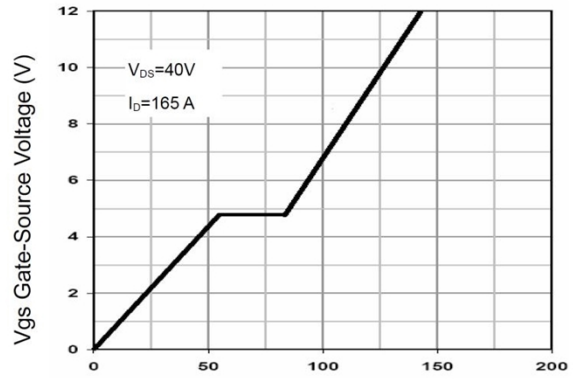
V_{ds} -Drain-Source Voltage (V)
Output Characteristics



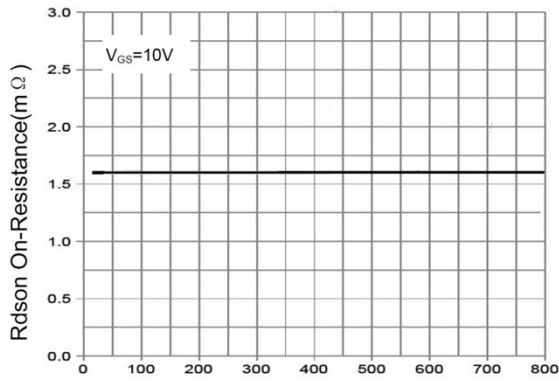
T_J -Junction Temperature ($^{\circ}\text{C}$)
 R_{dson} -Junction Temperature



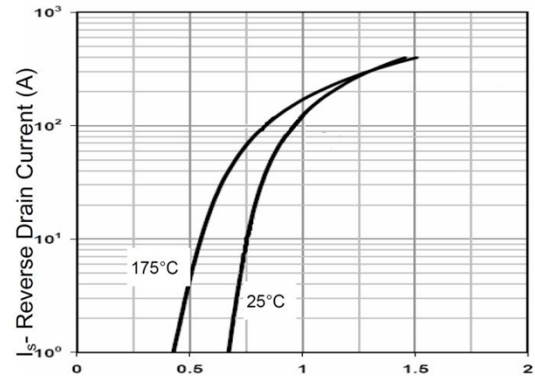
V_{gs} -Gate-Source Voltage (V)
Transfer Characteristics



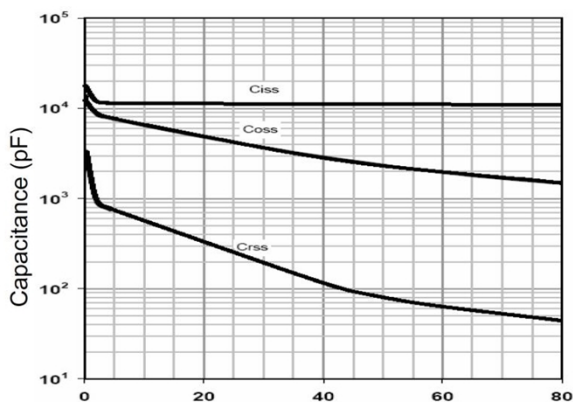
Q_g -Gate Charge (nC)
Gate Charge



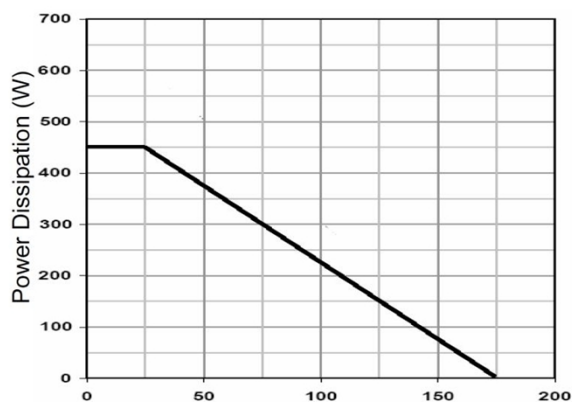
I_D -Drain Current (A)
 R_{dson} -Drain Current



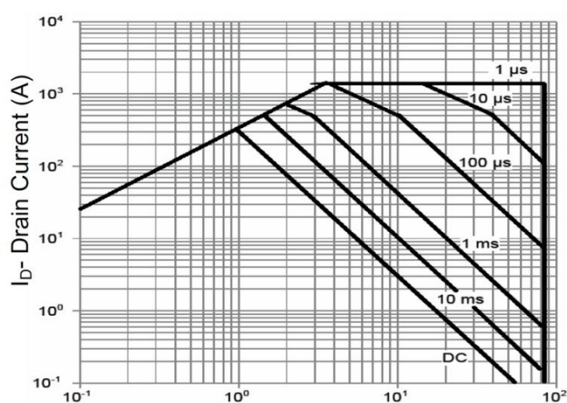
V_{sd} Source-Drain Voltage (V)
Source-Drain Diode Forward



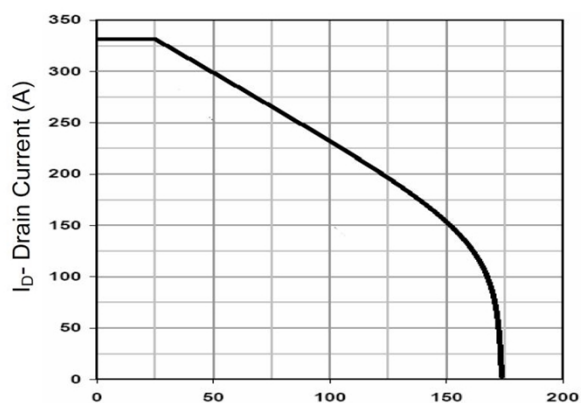
Vds Drain-Source Voltage (V)
Capacitance vs Vds



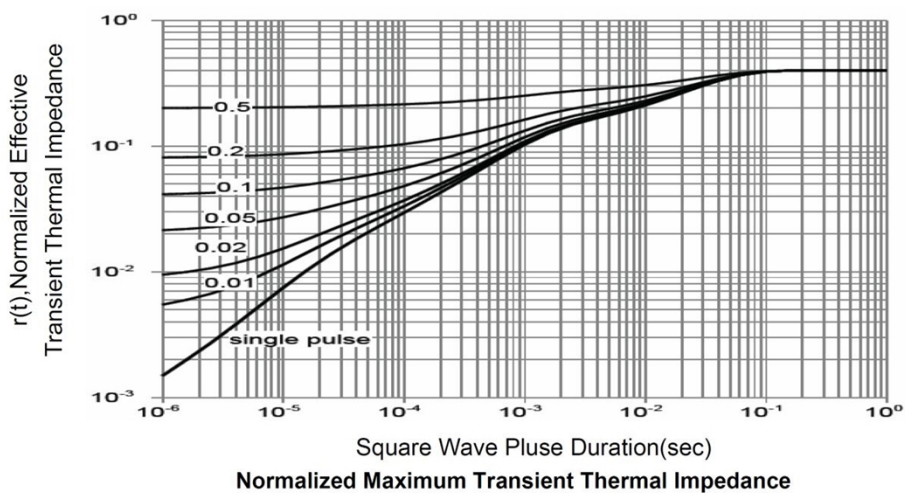
Tj-Junction Temperature(°C)
Power De-rating



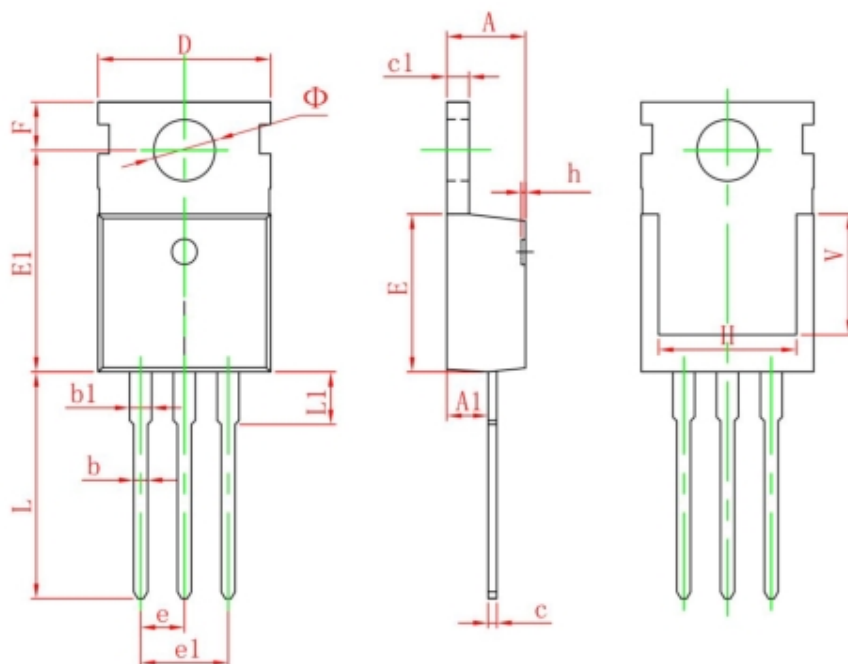
Vds Drain-Source Voltage (V)
Safe Operation Area



Tj-Junction Temperature (°C)
Current De-rating



TO-220-3L-C Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900 REF.		0.276 REF.	
Φ	3.400	3.800	0.134	0.150